November 1999



FDC637AN

Single N-Channel, 2.5V Specified PowerTrench[™] MOSFET

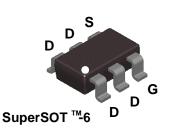
General Description

This N-Channel 2.5V specified MOSFET is produced using Fairchild Semiconductor's advanced PowerTrench process that has been especially tailored to minimize on-state resistance and yet maintain low gate charge for superior switching performance.

These devices have been designed to offer exceptional power dissipation in a very small footprint compared with bigger SO-8 and TSSOP-8 packages.

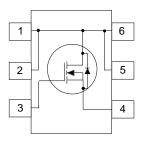
Applications

- DC/DC converter
- Load switch
- Battery Protection



Features

- 6.2 A, 20 V. $R_{DS(on)} = 0.024 \ \Omega \ @ V_{GS} = 4.5 \ V$ $R_{DS(on)} = 0.032 \ \Omega \ @ V_{GS} = 2.5 \ V$
- Fast switching speed.
- Low gate charge (10.5nC typical).
- High performance trench technology for extremely low $R_{\mbox{\tiny DS(ON)}}.$
- SuperSOT[™]-6 package: small footprint (72% smaller than standard SO-8); low profile (1mm thick).



Absolute Maximum Ratings T_A = 25°C unless otherwise noted

Symbol	Parameter		FDC637AN	Units		
V _{DSS}	Drain-Source Voltage			20	V	
V _{GSS}	Gate-Source Voltage			±8	V	
I _D	Drain Current - Continuous		(Note 1a)	6.2	A	
	Drain Current - Pulsed			20		
P _D	Power Dissipation for Sing	for Single Operation (Note 1a) 1.6		1.6	W	
			(Note 1b)	0.8		
	Operating and Storage Junction Temperature Range					
T _J , T _{stg}	Operating and Storage Ju	nction Temperature	Range	-55 to +150	°C	
Therma	Operating and Storage Jun I Characteristics Thermal Resistance, Junc		(Note 1a)	-55 to +150 78	°C W/S°	
	Characteristics	tion-to-Ambient			°C/W	
Therma _{RθJA} RθJC Packag	I Characteristics Thermal Resistance, Junc Thermal Resistance, Junc e Outlines and Or	tion-to-Ambient	(Note 1a) (Note 1)	78		

Symbol	Parameter	Test Conditions	Min	Тур	Max	Units
Off Char	acteristics					
BV _{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0~V,~I_D=250~\mu A$	20			V
<u>ΔBVdss</u> ΔTj	Breakdown Voltage Temperature Coefficient	$I_D = 250\mu A$, Referenced to $25^{\circ}C$		14		mV/°C
I _{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 16 \text{ V}, V_{GS} = 0 \text{ V}$			1	μA
I _{GSSF}	Gate-Body Leakage Current, Forward	$V_{GS} = 8 \text{ V}, V_{DS} = 0 \text{ V}$			100	nA
I _{GSSR}	Gate-Body Leakage Current, Reverse	V_{GS} = -8 V, V_{DS} = 0 V			-100	nA
On Char	acteristics (Note 2)					
V _{GS(th)}	Gate Threshold Voltage	$V_{DS} = V_{GS}$, $I_D = 250 \ \mu A$	0.4	0.82	1.5	V
<u>ΔV_{GS(th)}</u> ΔT _J	Gate Threshold Voltage Temperature Coefficient	I_D =250µA,Referenced to 125°C		-3		mV/°C
R _{DS(on)}	Static Drain-Source On-Resistance	$ \begin{array}{l} V_{GS} = 4.5 \ V, I_{D} = 6.2 \ A \\ V_{GS} = 4.5 \ V, I_{D} = 6.2 \ A, T_{J} = 125^{\circ}C \\ V_{GS} = 2.5 \ V, \ I_{D} = 5.2 \ A \end{array} $		0.019 0.028 0.025	0.024 0.041 0.032	Ω
D(on)	On-State Drain Current	$V_{GS} = 4.5 \text{ V}, V_{DS} = 5 \text{ V}$	10			Α
9 _{FS}	Forward Transconductance	$V_{DS} = 5 \text{ V}, \text{ I}_{D} = 6.2 \text{ A}$		7.4		S
Dvnamio	Characteristics					
C _{iss}	Input Capacitance	$V_{DS} = 10 \text{ V}, V_{GS} = 0 \text{ V},$		1125		pF
C _{oss}	Output Capacitance	f = 1.0 MHz		290		pF
C _{rss}	Reverse Transfer Capacitance			145		pF
Switchir	g Characteristics (Note 2)					
d(on)	Turn-On Delay Time	$V_{DD} = 10 \text{ V}, I_D = 1 \text{ A},$	1	9	18	ns
t r	Turn-On Rise Time	V_{GS} = 4.5 V, R_{GEN} = 6 Ω		13	24	ns
d(off)	Turn-Off Delay Time			26	42	ns
f	Turn-Off Fall Time			11	20	ns
Qg	Total Gate Charge	$V_{DS} = 5 V, I_D = 6.2 A,$		10.5	16	nC
Q _{gs}	Gate-Source Charge	V _{GS} = 4.5 V		1.5		nC
ସ _{ୁସ}	Gate-Drain Charge			2.2		nC
Drain-So	ource Diode Characteristics a	nd Maximum Ratings				
ls	Maximum Continuous Drain-Source Diode Forward Current		[1.3	А
V _{SD}	Drain-Source Diode Forward Voltage	$V_{GS} = 0 V, I_S = 1.3 A$ (Note 2)		0.7	1.2	V

Notes:

1. $R_{\theta,JA}$ is the sum of the junction-to-case and case-to-ambient resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. $R_{\theta,JC}$ is guaranteed by design while $R_{\theta,CA}$ is determined by the user's board design.

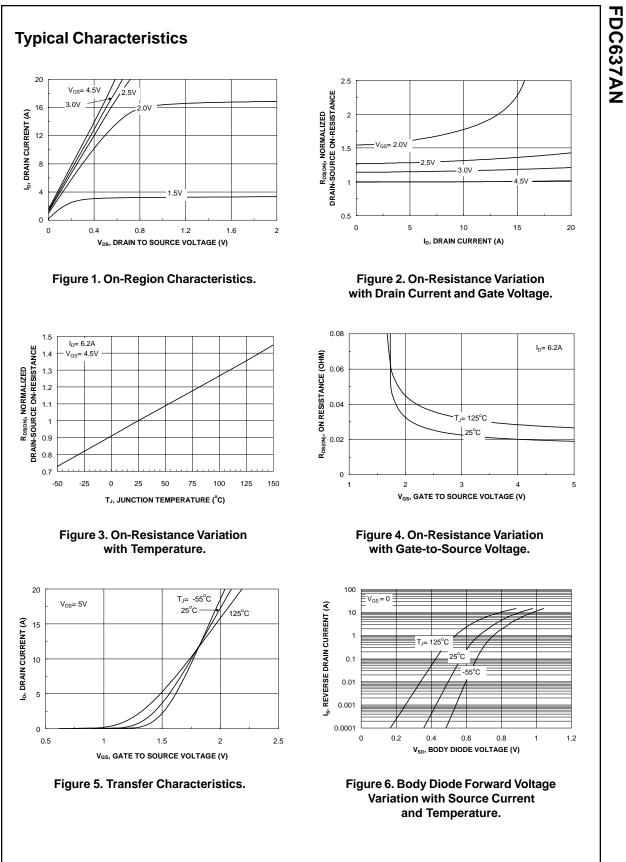
a) 78° C/W when mounted on a 1.0 in^2 pad of 2 oz. copper.

b) 156° C/W when mounted on a minimum pad of 2 oz.copper.

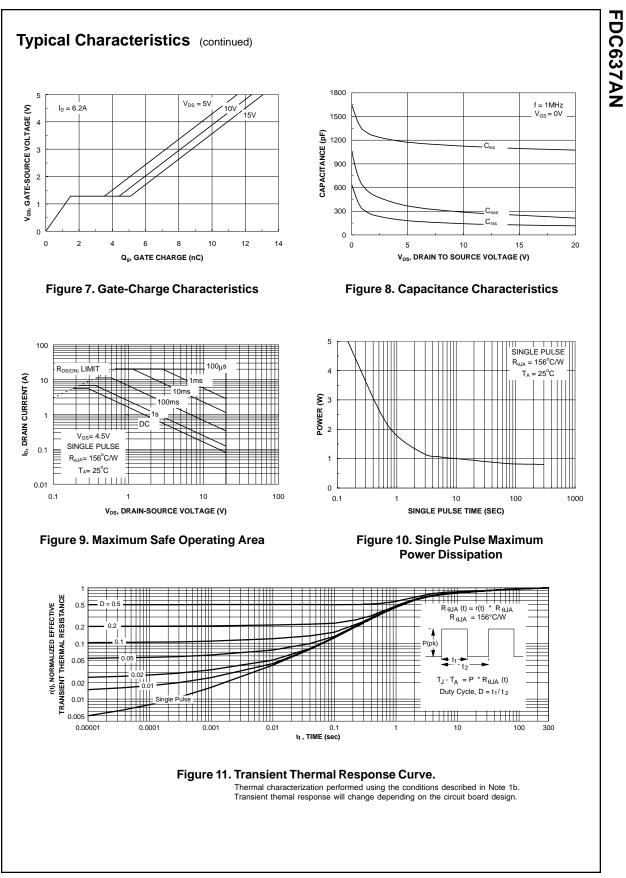
2. Pulse Test: Pulse Width $\leq 300~\mu\text{s},$ Duty Cycle $\leq 2.0\%$

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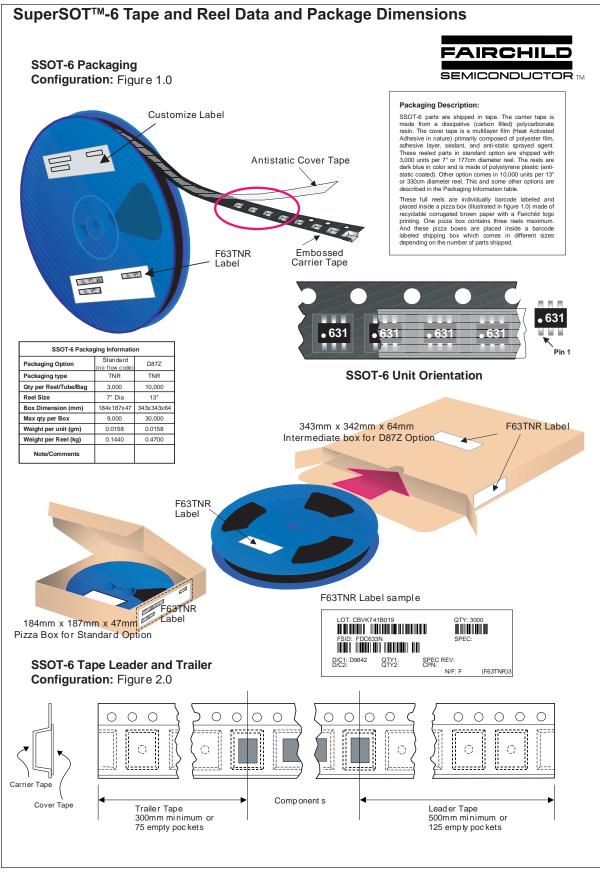
FDC637AN, Rev. C



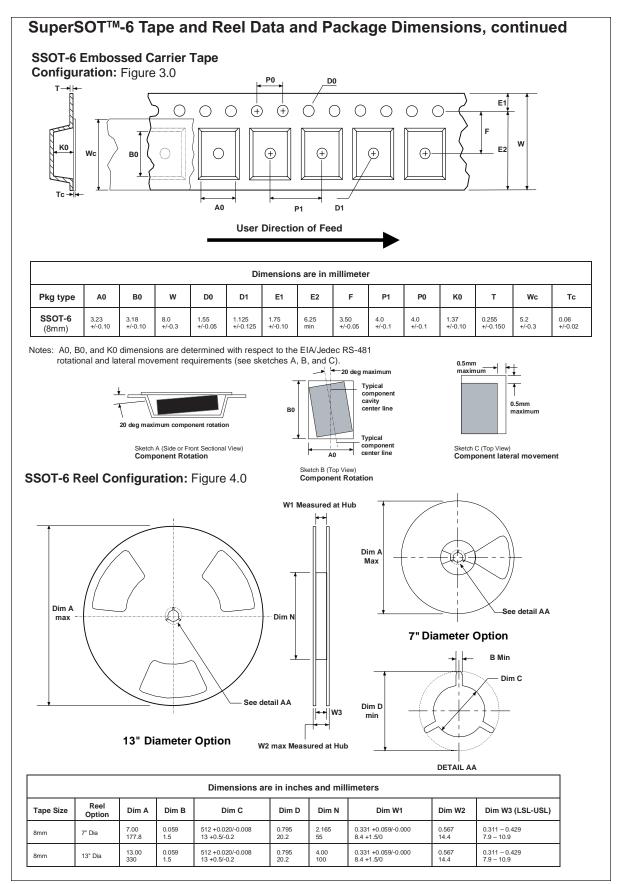
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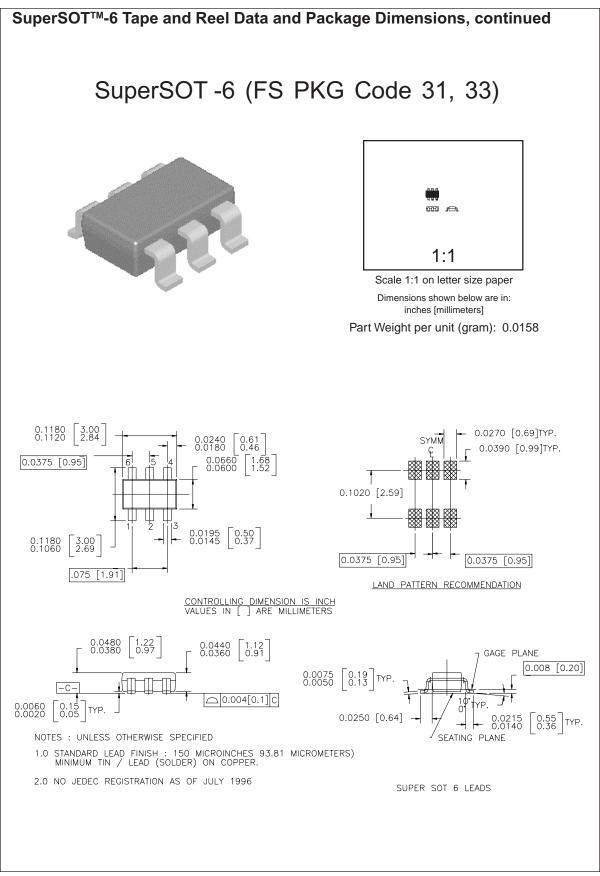
FDC637AN, Rev. C



August 1999, Rev. C



July 1999, Rev. C



September 1998, Rev. A

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